

Estimating Average Capacitances in CMOS circuits

For a particular transistor there are 2 capacitances of interest, the gate (C_g) and drain (C_d).

C_g can be estimated as:

$$C_g = W * L * C_{ox} \quad \text{where } C_{ox} = \text{the capacitance per unit area}$$

C_d is dependent on the layout of the drain but is also proportional to the width.

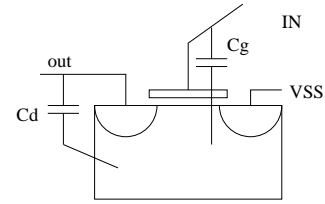
$$C_d \sim W * C_j \quad \text{where } C_j = \text{the junction capacitance per unit width of the drain}$$

Note: This is simplified from what you might see elsewhere.

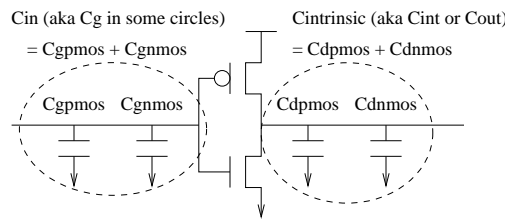
In many situations it is useful to define some base values of Capacitances (and Resistances) relative to the smallest transistor available.

$C_{g_{min}}$: The gate capacitance of a minimum sized transistor in a technology (eg. $W=220\mu\text{m}$, $L=180\mu\text{m}$ in 0.18um TSMC)

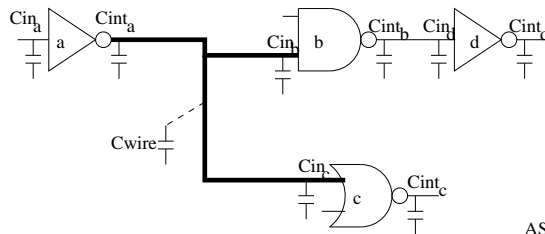
$C_{d_{min}}$: The drain capacitance of a minimum sized transistor in a technology (eg. $W=220\mu\text{m}$ in 0.18um TSMC)



Inside a gate, when we put the transistors together in a CMOS configuration, the individual capacitances can add together.



Then when we put GATES together we get intrinsic, input AND wiring capacitances added together



ASSUME:

All NMOS are minimum sized.

All PMOS are 2x min width, min length.

Unit wiring capacitance is $0.2 * C_{g_{min}} / \mu\text{m}$

$C_{d_{min}} = C_{g_{min}} / 4$

The highlighted net is 4 um long.

Example:

What is the total capacitance on the highlighted net, in terms of $C_{g_{min}}$?

$$\begin{aligned} C_{net} &= C_{int_a} + C_{in_b} + C_{in_c} + C_{wire} \\ &= (C_{d_{min}} + 2C_{d_{min}}) + (C_{g_{min}} + 2C_{g_{min}}) + (C_{g_{min}} + 2C_{g_{min}}) + 4 * 0.2 * C_{g_{min}} \\ &= 0.75 C_{g_{min}} + 6 C_{g_{min}} + 0.8 C_{g_{min}} \\ &= 7.55 C_{g_{min}} \end{aligned}$$

Example:

The data sheets for a standard cell inverter specify that it has an input capacitance of 6 fF and output capacitance of 3fF. From some clever reverse engineering you've figured out that the PMOS is $2.200\mu\text{m} / 0.180\mu\text{m}$ and NMOS is $1.180\mu\text{m} / 0.180\mu\text{m}$. Minimum gate length is 0.18 um, width is 0.22um.

What is $C_{g_{min}}$ and $C_{d_{min}}$?

$$\begin{aligned} C_{in} &= C_{g_{pmos}} + C_{g_{nmos}} \\ 6\text{fF} &= 10 * C_{g_{min}} + (1180/220) C_{g_{min}} \\ 6\text{fF} &= 18.18 C_{g_{min}} \\ C_{g_{min}} &= 0.330 \text{ fF} \end{aligned}$$

$$\begin{aligned} C_{out} = C_{int} &= C_{d_{pmos}} + C_{d_{nmos}} \\ 3 \text{ fF} &= 10 C_{d_{min}} + (1180/220) C_{d_{min}} \\ C_{d_{min}} &= 0.165 \text{ fF} \end{aligned}$$

Conclusion:

When referring to digital gates, we simplify capacitances in terms of an input (C_{in}) and output/intrinsic capacitance (C_{int}).

Given relative transistor sizing in a system, you should be able to determine the capacitance on each net in terms of $C_{g_{min}}$ and $C_{d_{min}}$.